Optimization of FIB lamellas preparation for gate-oxide pinholes characterization

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The FIB sample preparation for Transmission Electron Microscopy is a well established technique and usually thinner is better.

In semiconductor industry this rule is often not true because the purpose is not necessarily to make a very good image but to find a physical defect in correspondence of electrical failing position. In this work we demonstrate that leaving the sample thick is the right choice for gate-oxide pinhole characterization